N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} 40V
- I_D 100A
- $R_{DS(ON)}$(at V_{GS}=10V) Parameter Symbol

				Limit	Unit
Drain-source Voltage			V_{DS}	40	V
Gate-source Voltage			V_{GS}	±20	V
Continuous Drain Current (Note 1,2)	Steady-State	T_A=25	I_D	19	A
		T_A=100		13	
Continuous Drain Current (Note 1,3)	Steady-State	T_C=25		100	
		T_C =100		70	
Pulsed Drain Current	T_C=25 , t_p=100μs		I_{DM}	400	A
Avalanche energy	V_G=10V, R_G=25Ω, L=0.5mH, IAS=25.4A		EAS	161.29	mJ
Total Power Dissipation (Note 1,2)	Steady-State	T_A=25	P_D	2.7	W
		T_A=100		1.3	
Total Power Dissipation (Note 1,3)	Steady-State				

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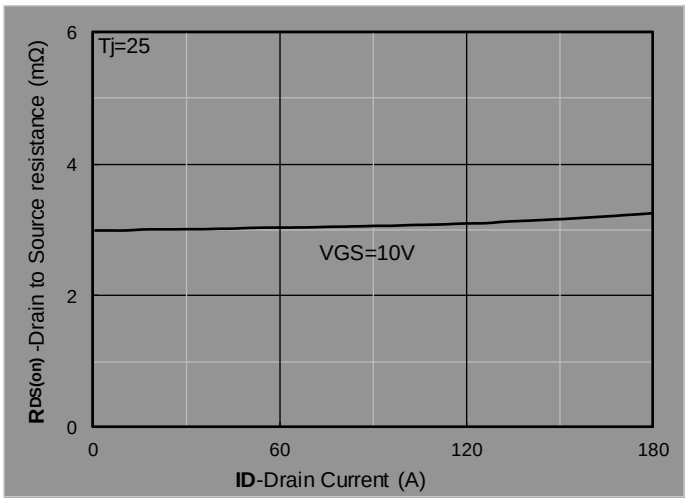
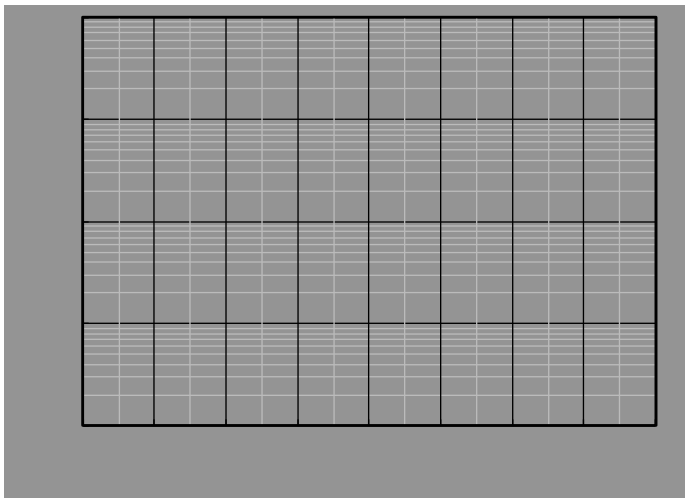
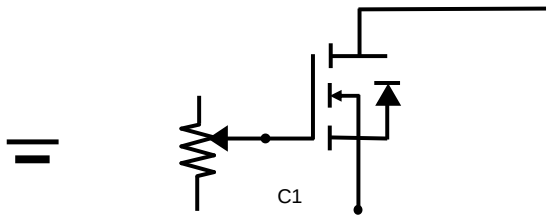

Tj=25
VGS=10V
RDS(on) -Drain to Source resistance (mΩ)
ID-Drain Current (A)
0
2
4
6
0
60
120
180





±55

5¦¢

■ TO-252-B Package information

SYMBOL	b MIN.	
	0.000	
A2		
b		0.030
c		
D		
D2		
E		
E1		